MOS FET Power Amplifier Module for DCS 1800 Handy Phone



ADE-208-432C (Z) 4th Edition December 1997

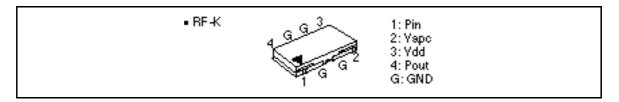
#### Application

For DCS 1800 class1 1710 to 1785 MHz.

#### Features

- 3stage amplifier : 0 dBm input
- Lead less thin & small package : 2 mm Max & 0.2cc
- High efficiency : 40% Typ at 32.5 dBm
- Wide gain control range : 70 dB Typ
- Low voltage operation : 3.5 V

#### **Pin Arrangement**



### **Absolute Maximum Ratings** (Tc = 25°C)

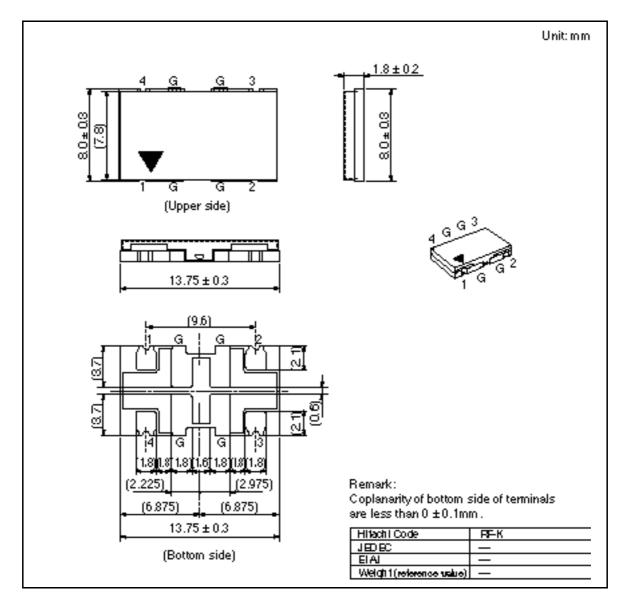
Item	Symbol	Rating	Unit	
Supply voltage	V <sub>dd</sub>	8	V	
Supply current	I <sub>DD</sub>	2	А	
V <sub>APC</sub> voltage	V <sub>APC</sub>	4	V	
Input power	Pin	10	mW	
Operating case temperature	Тс (ор)	-30 to +100	°C	
Storage temperature	Tstg	-30 to +100	°C	
Output power	Pout	3	W	



ltem	Symbol	Min	Тур	Max	Unit	Test Condition
Frequency range	f	1710		1785	MHz	
Control voltage range	V <sub>APC</sub>	0.5		2.2	V	
Drain cutoff current	I <sub>DS</sub>	—		100	μA	$V_{DD} = 8 \text{ V},  V_{APC} = 0 \text{ V}$
Total efficiency	т	35	40	_	%	$Pin = 0 dBm, V_{DD} = 3.5 V,$
2nd harmonic distortion	2nd H.D.	_	-45	-35	dBc	Pout = 32.5 dBm (at APC controlled),
3rd harmonic distortion	3rd H.D.		-45	-35	dBc	$R_{L} = Rg = 50$ , $Tc = 25^{\circ}C$
Input VSWR	VSWR (in)	_	1.5	3	_	-
Output power (1)	Pout (1)	32.5	33.0	_	dBm	$ \begin{array}{l} \mbox{Pin} = 0 \ \mbox{dBm}, \ \mbox{V}_{\mbox{\tiny DD}} = 3.5 \ \mbox{V}, \\ \mbox{V}_{\mbox{\tiny APC}} = 2.2 \ \mbox{V}, \ \mbox{R}_{\mbox{\tiny L}} = \mbox{R}g = 50 \ \ \ , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array} , $
Output power (2)	Pout (2)	31	31.5	_	dBm	$ \begin{array}{l} \mbox{Pin} = 0 \ \mbox{dBm}, \ \mbox{V}_{_{DD}} = 3.0 \ \mbox{V}, \\ \mbox{V}_{_{APC}} = 2.2 \ \mbox{V}, \ \mbox{R}_{_{L}} = \mbox{R}g = 50 \ \ \ , \\ \mbox{Tc} = 85^{\circ}\mbox{C} \end{array} , $
Isolation	_	—	-36	-33	dBm	$ \begin{array}{l} \mbox{Pin} = 0 \ \mbox{dBm}, \ \mbox{V}_{_{DD}} = 3.5 \ \mbox{V}, \\ \mbox{V}_{_{APC}} = 0.5 \ \mbox{V}, \ \mbox{R}_{_{L}} = \mbox{R}g = 50  , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array} $
Switching time	tr, tf	_	1	2	μs	$\begin{array}{l} \mbox{Pin} = 0 \ \mbox{dBm}, \ \mbox{V}_{\mbox{\tiny DD}} = 3.5 \ \mbox{V}, \\ \mbox{Pout} = 32.5 \ \mbox{dBm}, \ \mbox{R}_{\mbox{\tiny L}} = \mbox{Rg} = 50  , \\ \mbox{Tc} = 25^{\circ}\mbox{C} \end{array}$
Stability	_	No par oscillat			_	$\begin{array}{l} \mbox{Pin}=0\ dBm,\ V_{\mbox{\tiny DD}}=3\ to\ 5.1\ V,\\ \mbox{Pout} 32.5\ dBm\ (at\ APC\ controlled),\\ \mbox{Rg}=50,\ t=20\ sec.,\ Tc=25^{\circ}C,\\ \mbox{Output}\ VSWR=6:1\ All\ phases \end{array}$

# **Electrical Characteristics** (Tc = 25°C)

# **Package Dimensions**



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